

# ON Semiconductor

## Is Now

# onsemi™

To learn more about onsemi™, please visit our website at  
[www.onsemi.com](http://www.onsemi.com)

---

**onsemi** and **onsemi** and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi** product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner. Other names and brands may be claimed as the property of others.



ON Semiconductor®

# FDP027N08B

## N-Channel PowerTrench® MOSFET

80 V, 223 A, 2.7 mΩ

### Features

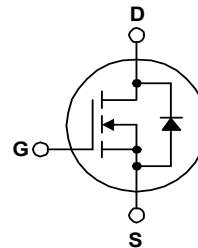
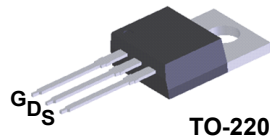
- $R_{DS(on)} = 2.21 \text{ m}\Omega$  (Typ.) @  $V_{GS} = 10 \text{ V}$ ,  $I_D = 100 \text{ A}$
- Low FOM  $R_{DS(on)} * Q_G$
- Low Reverse-Recovery Charge,  $Q_{rr} = 112 \text{ nC}$
- Soft Reverse-Recovery Body Diode
- Enables High Efficiency in Synchronous Rectification
- Fast Switching Speed
- 100% UIL Tested
- This device is Pb-Free, Halogen Free/BFR Free and is RoHS Compliant

### Description

This N-Channel MOSFET is produced using ON Semiconductor's PowerTrench® process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

### Applications

- Synchronous Rectification for ATX / Server / Telecom PSU
- Battery Protection Circuit
- Motor Drives and Uninterruptible Power Supplies



### MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FDP027N08B_F102	Unit
$V_{DSS}$	Drain to Source Voltage	80	V
$V_{GSS}$	Gate to Source Voltage	$\pm 20$	V
$I_D$	Drain Current	- Continuous ( $T_C = 25^\circ\text{C}$ , Silicon Limited)	223*
		- Continuous ( $T_C = 100^\circ\text{C}$ , Silicon Limited)	158*
		- Continuous ( $T_C = 25^\circ\text{C}$ , Package Limited)	120
$I_{DM}$	Drain Current	- Pulsed (Note 1)	892
$E_{AS}$	Single Pulsed Avalanche Energy	(Note 2)	917
$dv/dt$	Peak Diode Recovery $dv/dt$	(Note 3)	6.0
$P_D$	Power Dissipation	( $T_C = 25^\circ\text{C}$ )	246
		- Derate Above $25^\circ\text{C}$	1.64
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +175	$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

\*Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 120 A.

### Thermal Characteristics

Symbol	Parameter	FDP027N08B_F102	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.61	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

FDP027N08B — N-Channel PowerTrench® MOSFET

## Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDP027N08B-F102	FDP027N08B	TO-220	Tube	N/A	N/A	50 units

## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
--------	-----------	-----------------	------	------	------	------

### Off Characteristics

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250 \mu\text{A}, V_{GS} = 0 \text{V}$	80	-	-	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$ , Referenced to $25^\circ\text{C}$	-	0.05	-	$\text{V}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 64 \text{V}, V_{GS} = 0 \text{V}$ $V_{DS} = 64 \text{V}, T_C = 150^\circ\text{C}$	-	-	1 500	$\mu\text{A}$
$I_{GSS}$	Gate to Body Leakage Current	$V_{GS} = \pm 20 \text{V}, V_{DS} = 0 \text{V}$	-	-	$\pm 100$	nA

### On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu\text{A}$	2.5	-	4.5	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10 \text{V}, I_D = 100 \text{A}$	-	2.21	2.7	$\text{m}\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 10 \text{V}, I_D = 100 \text{A}$	-	227	-	S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 40 \text{V}, V_{GS} = 0 \text{V},$ $f = 1 \text{MHz}$	-	10170	13530	pF
$C_{oss}$	Output Capacitance		-	1670	2220	pF
$C_{riss}$	Reverse Transfer Capacitance		-	35	-	pF
$C_{oss(er)}$	Energy Related Output Capacitance	$V_{DS} = 40 \text{V}, V_{GS} = 0 \text{V}$	-	3025	-	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 40 \text{V}, V_{GS} = 10 \text{V},$ $I_D = 100 \text{A}$	-	137	178	nC
$Q_{gs}$	Gate to Source Gate Charge		-	56	-	nC
$Q_{gs2}$	Gate Charge Threshold to Plateau		-	25	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge		(Note 4)	-	28	-
ESR	Equivalent Series Resistance (G-S)	$f = 1 \text{MHz}$	-	2.4	-	$\Omega$

### Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 40 \text{V}, I_D = 100 \text{A},$ $V_{GS} = 10 \text{V}, R_G = 4.7 \Omega$	-	47	104	ns
$t_r$	Turn-On Rise Time		-	66	142	ns
$t_{d(off)}$	Turn-Off Delay Time		-	87	184	ns
$t_f$	Turn-Off Fall Time		(Note 4)	-	41	92

### Drain-Source Diode Characteristics

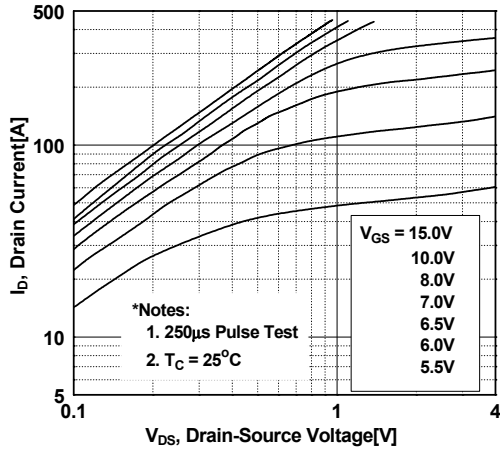
$I_S$	Maximum Continuous Drain to Source Diode Forward Current	-	-	223*	A	
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current	-	-	892	A	
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS} = 0 \text{V}, I_{SD} = 100 \text{A}$	-	-	1.3	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0 \text{V}, V_{DD} = 40 \text{V}, I_{SD} = 100 \text{A},$	-	80	-	ns
$Q_{rr}$	Reverse Recovery Charge	$di_F/dt = 100 \text{A}/\mu\text{s}$	-	112	-	nC

#### Notes:

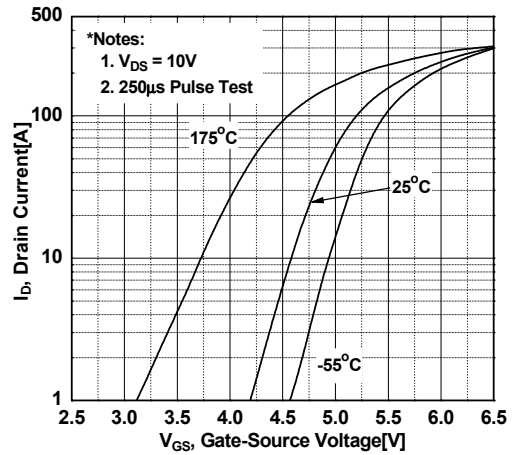
1. Repetitive rating: pulse-width limited by maximum junction temperature.
2.  $L = 3 \text{mH}, I_{AS} = 24.72 \text{A}, R_G = 25 \Omega$ , starting  $T_J = 25^\circ\text{C}$ .
3.  $I_{SD} \leq 100 \text{A}, di/dt \leq 200 \text{A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , starting  $T_J = 25^\circ\text{C}$ .
4. Essentially independent of operating temperature typical characteristics.

## Typical Performance Characteristics

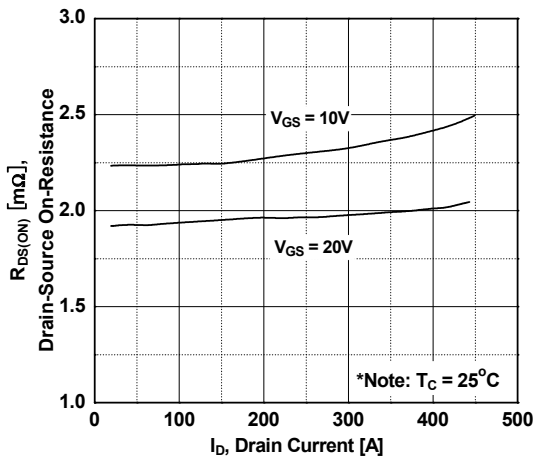
**Figure 1. On-Region Characteristics**



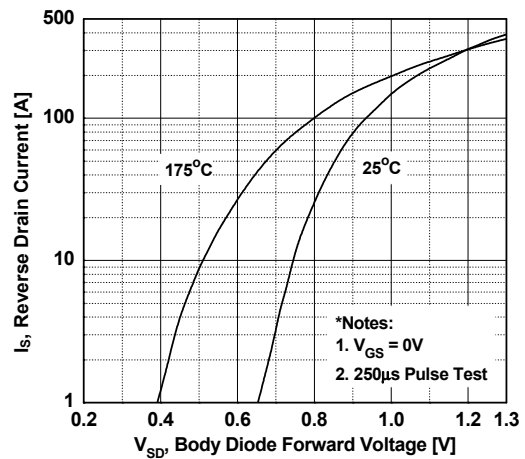
**Figure 2. Transfer Characteristics**



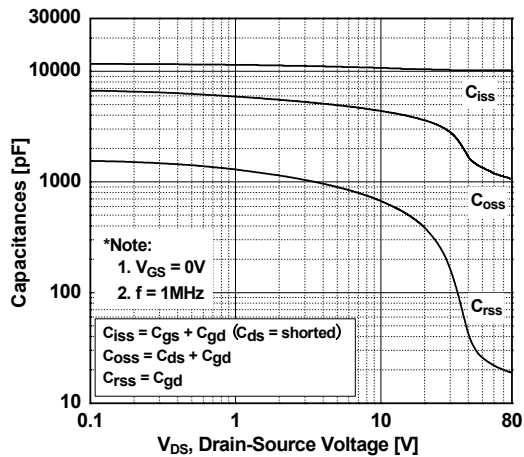
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



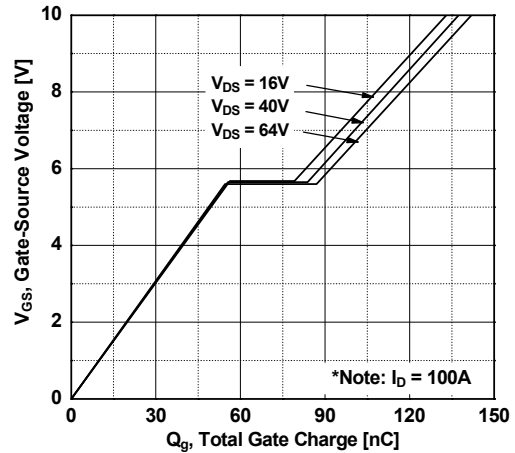
**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**



**Figure 5. Capacitance Characteristics**

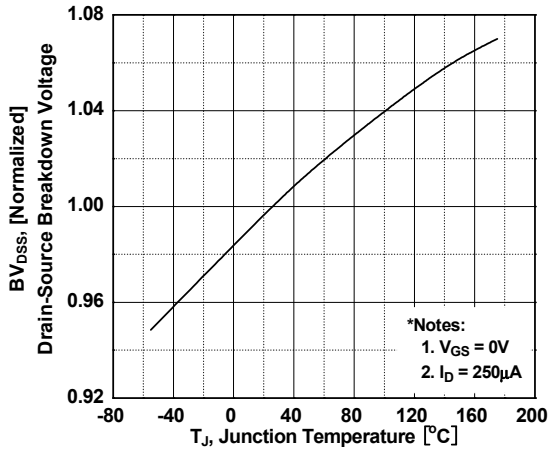


**Figure 6. Gate Charge Characteristics**

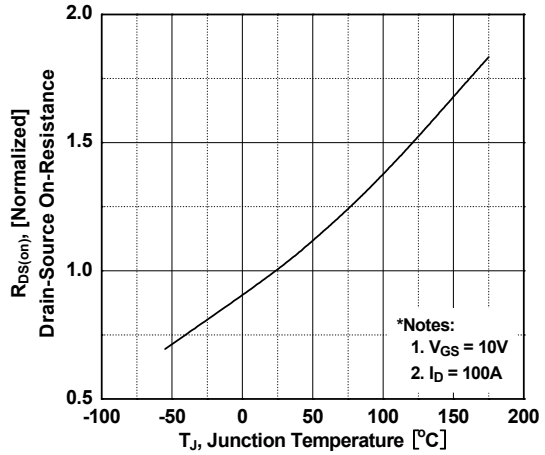


## Typical Performance Characteristics (Continued)

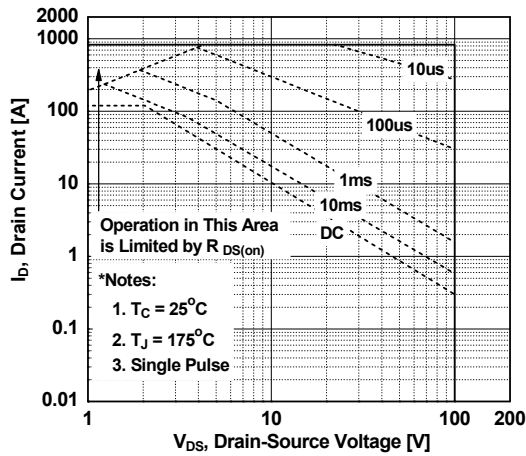
**Figure 7. Breakdown Voltage Variation vs. Temperature**



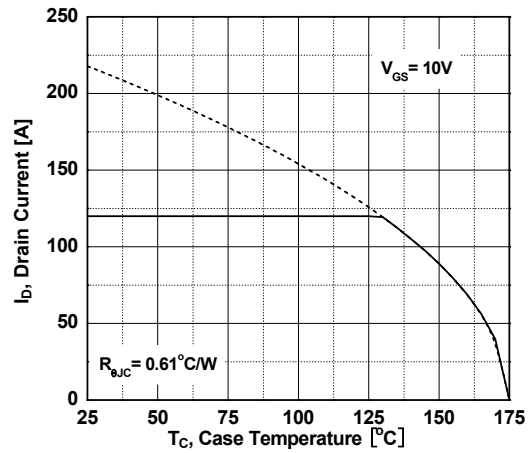
**Figure 8. On-Resistance Variation vs. Temperature**



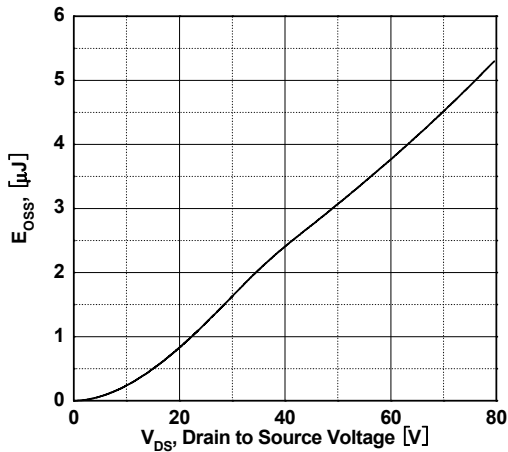
**Figure 9. Maximum Safe Operating Area**



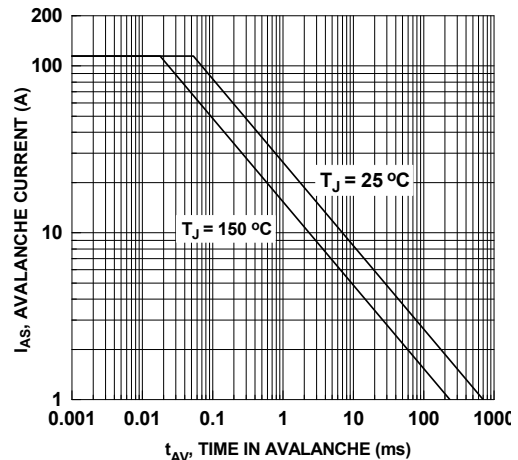
**Figure 10. Maximum Drain Current vs. Case Temperature**



**Figure 11. E\_oss vs. Drain to Source Voltage**

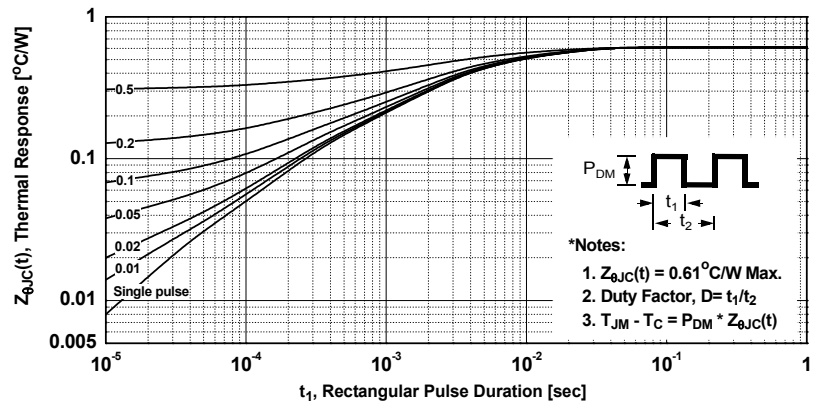


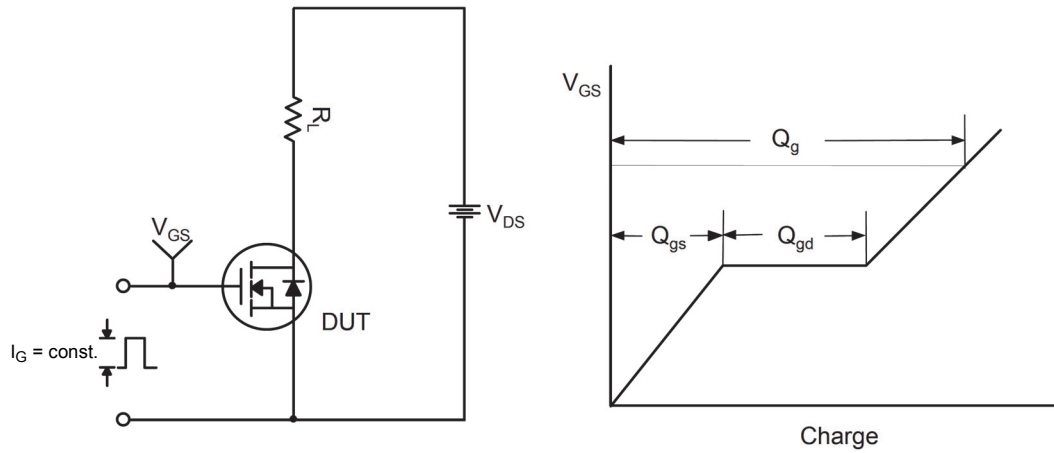
**Figure 12. Unclamped Inductive Switching Capability**



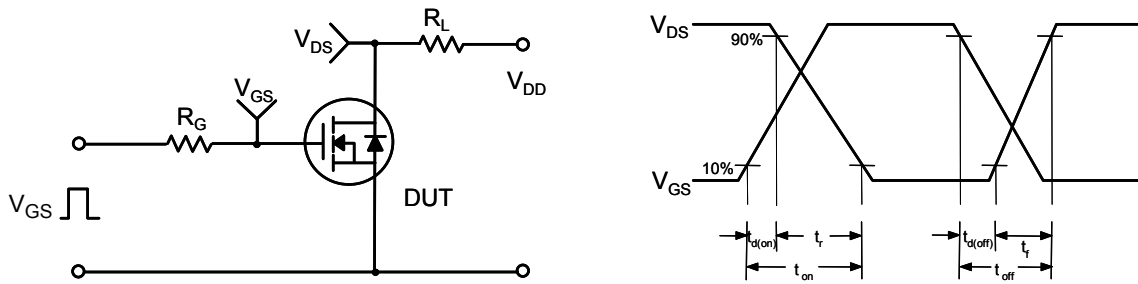
Typical Performance Characteristics (Continued)

Figure 13. Transient Thermal Response Curve





**Figure 14. Gate Charge Test Circuit & Waveform**



**Figure 15. Resistive Switching Test Circuit & Waveforms**



**Figure 16. Unclamped Inductive Switching Test Circuit & Waveforms**

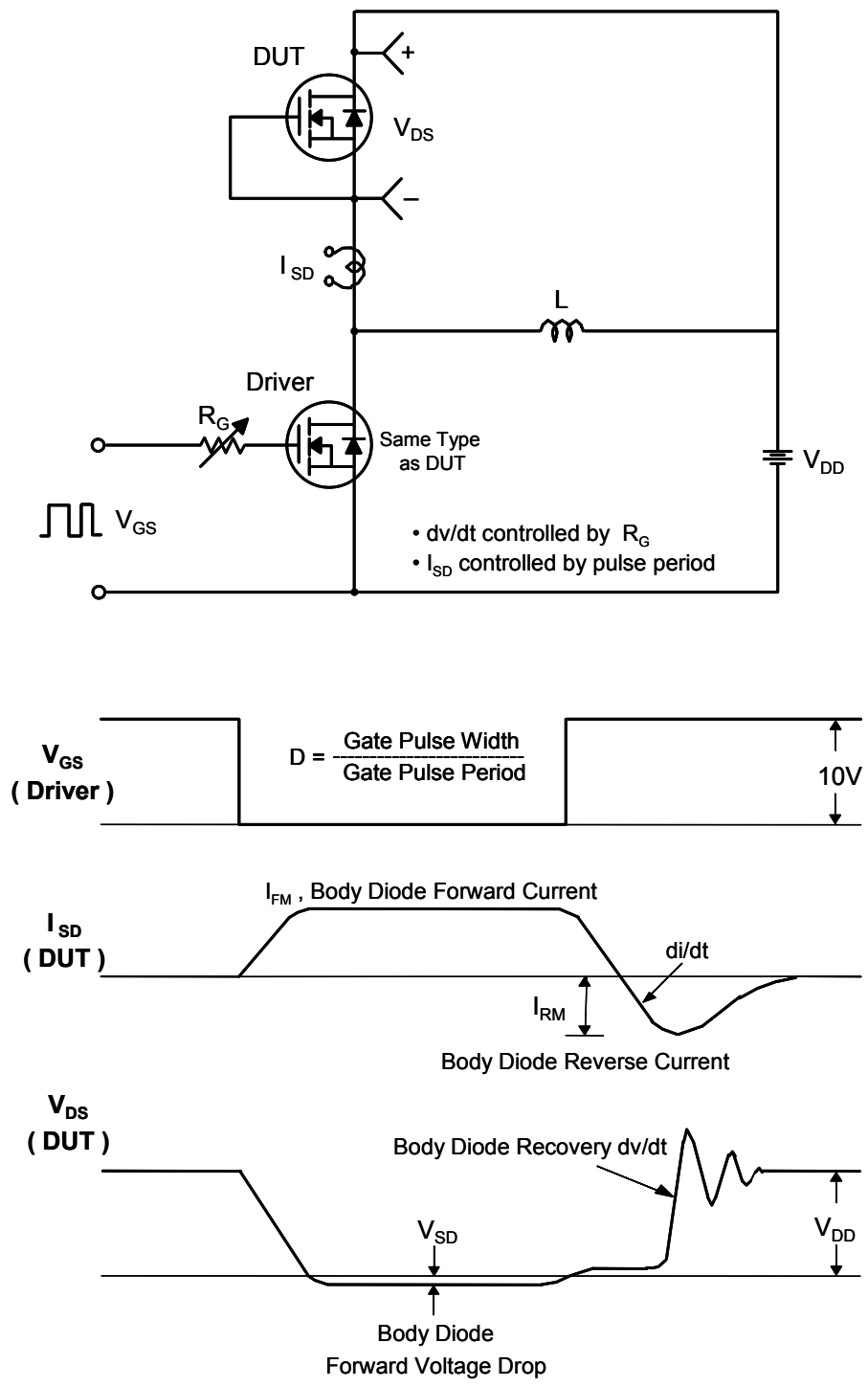
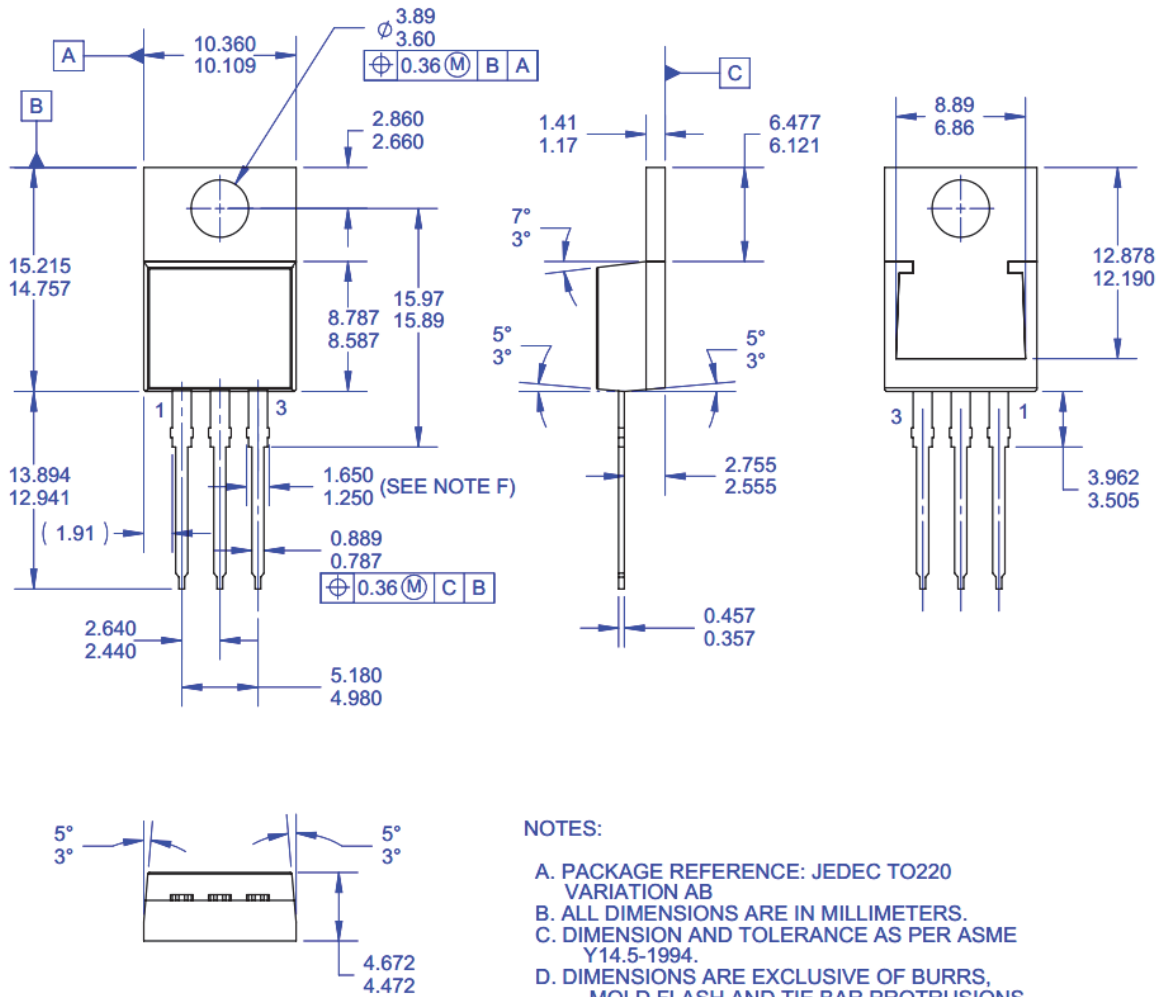


Figure 17. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms



## Mechanical Dimensions



**Figure 18. TO-220, Molded, 3-Lead, Jedec Variation AB (Delta)**

Package drawings are provided as a service to customers considering ON Semiconductor components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a ON Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of ON Semiconductor's worldwide terms and conditions, specifically the warranty therein, which covers ON Semiconductor products.

Always visit ON Semiconductor's online packaging area for the most recent package drawings: [www.onsemi.com](http://www.onsemi.com)

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## PUBLICATION ORDERING INFORMATION

### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor  
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA  
**Phone:** 303-675-2175 or 800-344-3860 Toll Free USA/Canada  
**Fax:** 303-675-2176 or 800-344-3867 Toll Free USA/Canada  
**Email:** [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

**N. American Technical Support:** 800-282-9855 Toll Free  
USA/Canada  
**Europe, Middle East and Africa Technical Support:**  
Phone: 421 33 790 2910

**ON Semiconductor Website:** [www.onsemi.com](http://www.onsemi.com)

**Order Literature:** <http://www.onsemi.com/orderlit>

For additional information, please contact your local  
Sales Representative

# Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[onsemi:](#)

[FDP027N08B-F102](#)